

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-21. (Canceled)

22. (Currently Amended) A method for manufacturing an article comprising:
selectively forming a release layer over a substrate,
forming a plurality of thin film integrated circuits over the release layer;
forming a first opening portion and a second opening portion at a boundary between the plurality of thin film integrated circuits adjacent to each other among the plurality of thin film integrated circuits, so that the plurality of thin film integrated circuits are connected to each other at a connection region between the first opening portion and the second opening portion;

pasting the plurality of thin film integrated circuits to a first substratum having an adhesion surface, the first substratum having a ~~second~~ third opening portion;

after pasting the plurality of thin film integrated circuits to ~~[[a]]~~ the first substratum, removing the release layer by introducing gas or liquid including halogen fluoride to the ~~first and second opening portions to remove the release layer~~ first, second and third opening portions, so that the plurality of thin film integrated circuits are fixed to the substrate at the connection region;

separating the substrate from the plurality of thin film integrated circuits; and
transposing the plurality of thin film integrated circuits to a second substratum having an adhesion surface with a higher adhesion strength than that of the adhesion surface of the first substratum,
wherein the first opening portion is overlapped with the ~~second~~ third opening portion.

23. (Original) The method according to claim 22, wherein the first substratum comprises silicon resin or fluorocarbon resin.

24. (Previously Presented) The method according to claim 22, wherein the first substratum is a roll having silicon resin or fluorocarbon resin thereon.

25. (Original) The method according to claim 22, wherein the second substratum is a flexible substrate or a protective film.

26. (Original) The method according to claim 22, wherein an antenna is formed over the second substratum.

27. (Original) The method according to claim 22, wherein the plurality of thin film integrated circuits comprise a semiconductor film with a thickness of 0.2 μm or less.

28. (Original) The method according claim 27, wherein the semiconductor film is crystallized by laser irradiation.

29. (Withdrawn/Currently Amended) A method for manufacturing an article comprising:

selectively forming a release layer over a substrate, the substrate comprising a first region on which the release layer is formed and a second region on which the release layer is not formed;

forming a plurality of thin film integrated circuits over the release layer ~~so that the plurality of thin film integrated circuits are fixated to the substrate in the second region;~~

forming a first opening portion and a second opening portion at a boundary between the plurality of thin film integrated circuits adjacent to each other among the

plurality of thin film integrated circuits, so that the plurality of thin film integrated circuits are connected to each other at a connection region between the first opening portion and the second opening portion;

 pasting the plurality of thin film integrated circuits to a first substratum having an adhesion surface, the first substratum having a ~~second~~ third opening portion;

 after pasting the plurality of thin film integrated circuits to ~~[[a]]~~ the first substratum, removing the release layer by introducing gas or liquid including halogen fluoride into the ~~first and second opening portions to remove the release layer~~ first, second and third opening portions, so that the plurality of thin film integrated circuits are fixed to the substrate at the connection region;

 separating the substrate from the plurality of thin film integrated circuits; and

 transposing the plurality of thin film integrated circuits to a second substratum having an adhesion surface with a higher adhesion strength than that of the adhesion surface of the first substratum,

 wherein the first opening portion is overlapped with the ~~second~~ third opening portion.

30. (Withdrawn) The method according to claim 29, wherein the first substratum comprises silicon resin or fluorocarbon resin.

31. (Withdrawn) The method according to claim 29, wherein the first substratum is a roll having silicon resin or fluorocarbon resin thereon.

32. (Withdrawn) The method according to claim 29, wherein the second substratum is a flexible substrate or a protective film.

33. (Withdrawn) The method according to claim 29, wherein an antenna is formed over the second substratum.

34. (Withdrawn) The method according to claim 29, wherein the plurality of thin film integrated circuits comprise a semiconductor film with a thickness of 0.2 μm or less.

35. (Withdrawn) The method according claim 34, wherein the semiconductor film is crystallized by laser irradiation.

36. (Currently Amended) A method for manufacturing an article comprising:
selectively forming a release layer over a substrate;
forming a plurality of thin film integrated circuits over the release layer;
forming a first opening portion and a second opening portion at a boundary between the plurality of thin film integrated circuits adjacent to each other among the plurality of thin film integrated circuits, so that the plurality of thin film integrated circuits are connected to each other at a connection region between the first opening portion and the second opening portion;

pasting the plurality of thin film integrated circuits to a first substratum having an adhesion surface, the first substratum having a ~~second~~ third opening portion;

after pasting the plurality of thin film integrated circuits to ~~[[a]]~~ the first substratum, removing the release layer by introducing gas or liquid including halogen fluoride into the ~~first and second opening portions to remove the release layer~~ first, second and third opening portions, so that the plurality of thin film integrated circuits are fixed to the substrate at the connection region;

separating the substrate from the plurality of thin film integrated circuits;

transposing the plurality of thin film integrated circuits to a second substratum having an adhesion surface with a higher adhesion strength than that of the adhesion surface of the first substratum; and

cutting the plurality of thin film integrated circuits at a boundary between the plurality of thin film integrated circuits adjacent to each other,

wherein the first opening portion is overlapped with the ~~second~~ third opening portion.

37. (Previously Presented) The method according to claim 36, wherein the first substratum comprises silicon resin or fluorocarbon resin.

38. (Previously Presented) The method according to claim 36, wherein the first substratum is a roll having silicon resin or fluorocarbon resin thereon.

39. (Previously Presented) The method according to claim 36, wherein the second substratum is a flexible substrate or a protective film.

40. (Previously Presented) The method according to claim 36, wherein an antenna is formed over the second substratum.

41. (Previously Presented) The method according to claim 36, wherein the plurality of thin film integrated circuits comprise a semiconductor film with a thickness of 0.2 μm or less.

42. (Previously Presented) The method according claim 41, wherein the semiconductor film is crystallized by laser irradiation.

43. (Currently Amended) A method for manufacturing an article comprising:
selectively forming a release layer over a substrate;
forming a plurality of thin film integrated circuits over the release layer;
forming a first opening portion and a second opening portion at a boundary between the plurality of thin film integrated circuits adjacent to each other among the plurality of thin film integrated circuits, so that the plurality of thin film integrated circuits

are connected to each other at a connection region between the first opening portion and the second opening portion;

 pasting the plurality of thin film integrated circuits to a first substratum having an adhesion surface, the first substratum having a ~~second~~ third opening portion;

 after pasting the plurality of thin film integrated circuits to ~~[[a]]~~ the first substratum, removing the release layer by introducing gas or liquid including halogen fluoride into the ~~first and second opening portions to remove the release layer~~ first, second and third opening portions, so that the plurality of thin film integrated circuits are fixed to the substrate at the connection region;

 separating the substrate from the plurality of thin film integrated circuits; and

 transposing the plurality of thin film integrated circuits to a second substratum having an adhesion surface with a higher adhesion strength than that of the adhesion surface of the first substratum;

 cutting the plurality of thin film integrated circuits at a boundary between the plurality of thin film integrated circuits adjacent to each other; and

 filling periphery of the plurality of thin film integrated circuits with an organic resin, wherein the first opening portion is overlapped with the ~~second~~ third opening portion.

44. (Previously Presented) The method according to claim 43, wherein the first substratum comprises silicon resin or fluorocarbon resin.

45. (Previously Presented) The method according to claim 43, wherein the first substratum is a roll having silicon resin or fluorocarbon resin thereon.

46. (Previously Presented) The method according to claim 43, wherein the second substratum is a flexible substrate or a protective film.

47. (Previously Presented) The method according to claim 43, wherein an antenna is formed over the second substratum.

48. (Previously Presented) The method according to claim 43, wherein the plurality of thin film integrated circuits comprise a semiconductor film with a thickness of 0.2 μm or less.

49. (Previously Presented) The method according claim 48, wherein the semiconductor film is crystallized by laser irradiation.